# **Complementary Silicon Plastic Power Transistors**

Designed for use in general purpose amplifier and switching applications.

#### **Features**

- High Current Gain Bandwidth Product
- Compact TO-220 Package
- These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	V <sub>CEO</sub>	40 60 80 100	Vdc
Collector-Base Voltage TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	V <sub>CB</sub>	40 60 80 100	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	3.0	Adc
Collector Current – Peak	I <sub>CM</sub>	5.0	Adc
Base Current	I <sub>B</sub>	1.0	Adc
Total Power Dissipation  @ T <sub>C</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	40 0.32	W W/°C
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	2.0 0.016	W W/°C
Unclamped Inductive Load Energy (Note 1)	E	32	mJ
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1.  $I_C = 1.8 \text{ A}, L = 20 \text{ mH}, P.R.F. = 10 \text{ Hz}, V_{CC} = 10 \text{ V}, R_{BE} = 100 \Omega$ 

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.125	°C/W

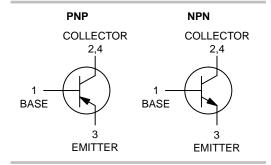
\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



#### ON Semiconductor®

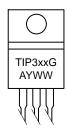
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# 3 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 40-60-80-100 VOLTS, 40 WATTS





#### **MARKING DIAGRAM**



TIP3xx = Device Code xx = 1, 1A, 1B, 1C, 2, 2A, 2B, 2C, A = Assembly Location

Y = Year WW = Work Week G Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 6 of this data sheet.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u> </u>			
Collector–Emitter Sustaining Voltage (Note 2) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 0) TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	V <sub>CEO(sus)</sub>	40 60 80 100	- - - -	Vdc
Collector Cutoff Current	I <sub>CEO</sub>	-	0.3 0.3	mAdc
Collector Cutoff Current $ (V_{CE} = 40 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP31G}, \text{TIP32G} $ $ (V_{CE} = 60 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP31AG}, \text{TIP32AG} $ $ (V_{CE} = 80 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP31BG}, \text{TIP32BG} $ $ (V_{CE} = 100 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP31CG}, \text{TIP32CG} $	I <sub>CES</sub>	- - -	200 200 200 200	μAdc
Emitter Cutoff Current $(V_{BE} = 5.0 \text{ Vdc}, I_C = 0)$	I <sub>EBO</sub>	-	1.0	mAdc
ON CHARACTERISTICS (Note 2)				
DC Current Gain ( $I_C = 1.0$ Adc, $V_{CE} = 4.0$ Vdc) ( $I_C = 3.0$ Adc, $V_{CE} = 4.0$ Vdc)	h <sub>FE</sub>	25 10	- 50	_
Collector–Emitter Saturation Voltage ( $I_C = 3.0 \text{ Adc}, I_B = 375 \text{ mAdc}$ )	V <sub>CE(sat)</sub>	-	1.2	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 4.0 Vdc)	V <sub>BE(on)</sub>	-	1.8	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)	f <sub>T</sub>	3.0	_	MHz
Small–Signal Current Gain (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	20	_	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

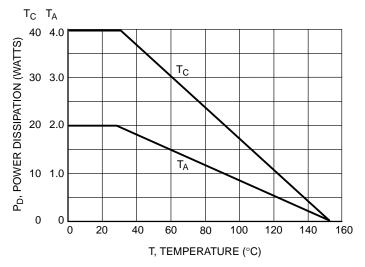
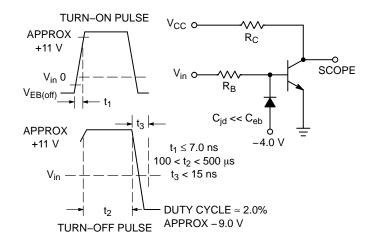
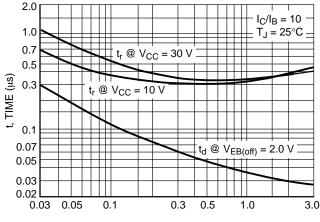


Figure 1. Power Derating



 ${\rm R}_{\rm B}$  and  ${\rm R}_{\rm C}$  VARIED TO OBTAIN DESIRED CURRENT LEVELS.

Figure 2. Switching Time Equivalent Circuit



 $I_C$ , COLLECTOR CURRENT (AMP)

Figure 3. Turn-On Time

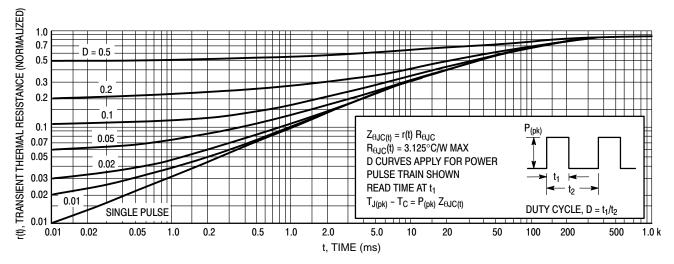


Figure 4. Thermal Response

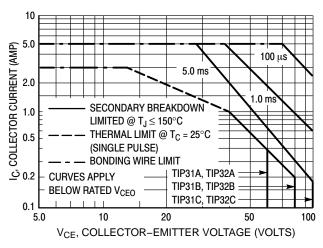


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

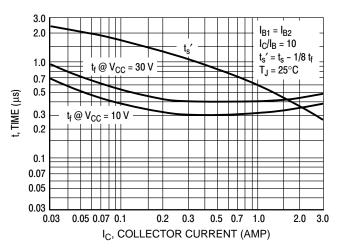


Figure 6. Turn-Off Time

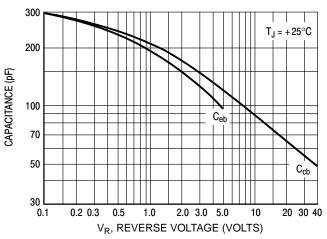
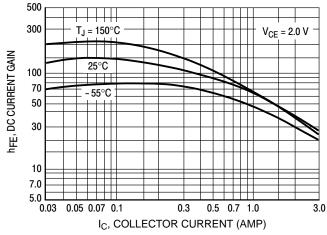


Figure 7. Capacitance



, COLLECTOR CURRENT (AMI

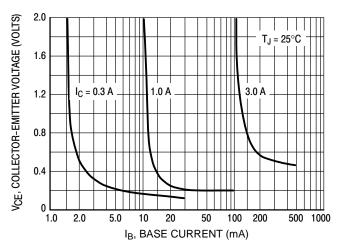


Figure 9. Collector Saturation Region

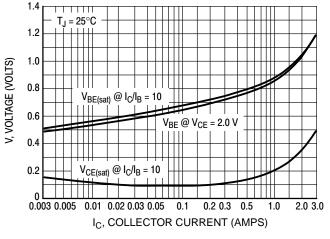


Figure 10. "On" Voltages

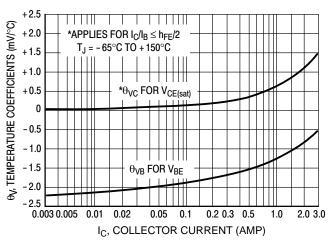


Figure 11. Temperature Coefficients

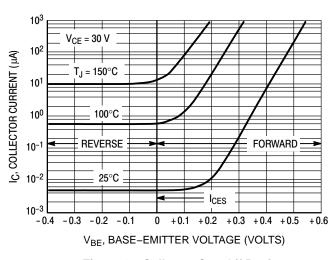


Figure 12. Collector Cut-Off Region

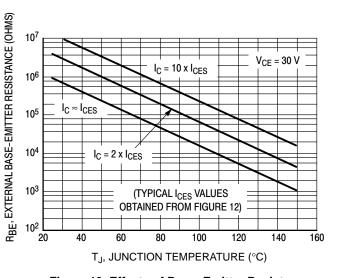
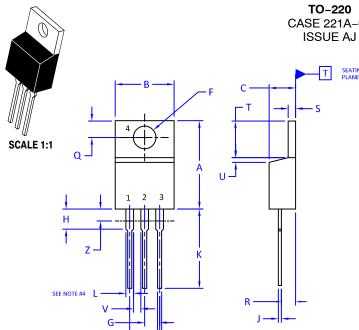


Figure 13. Effects of Base-Emitter Resistance

#### **ORDERING INFORMATION**

Device	Package	Shipping
TIP31G	TO-220 (Pb-Free)	50 Units / Rail
TIP31AG	TO-220 (Pb-Free)	50 Units / Rail
TIP31BG	TO-220 (Pb-Free)	50 Units / Rail
TIP31CG	TO-220 (Pb-Free)	50 Units / Rail
TIP32G	TO-220 (Pb-Free)	50 Units / Rail
TIP32AG	TO-220 (Pb-Free)	50 Units / Rail
TIP32BG	TO-220 (Pb-Free)	50 Units / Rail
TIP32CG	TO-220 (Pb-Free)	50 Units / Rail



CASE 221A-09

**DATE 05 NOV 2019** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

#### 4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELA
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11:		STYLE 12	:
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

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